

ZXMP6A17DN8
DUAL P-CHANNEL 60V ENHANCEMENT MODE MOSFET
Product Summary

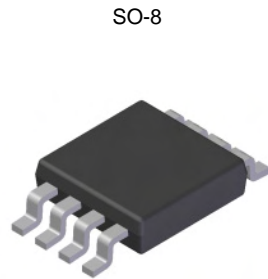
$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D $T_A = 25^\circ C$ (Notes 7 & 9)
-60V	125m Ω @ $V_{GS} = -10V$	-3.4A
	190m Ω @ $V_{GS} = -4.5V$	-2.8A

Description

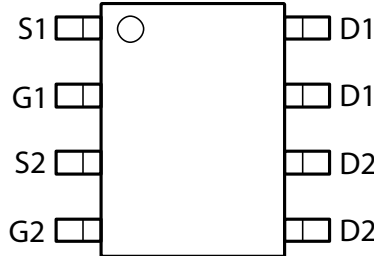
This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management functions
- Disconnect Switches
- Motor control



Top View



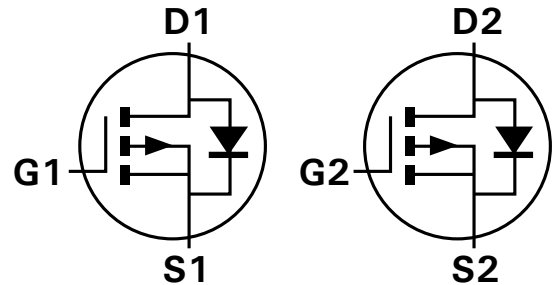
Top View

Features

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP capable (Note 4)**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)

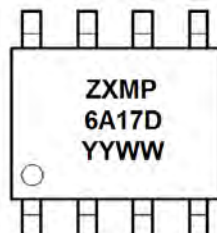


Equivalent Circuit

Ordering Information (Notes 4 & 5)

Product	Grade	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP6A17DN8TA	AEC-Q101	ZXMP6A17D	7	12	500
ZXMP6A17DN8QTA	Automotive	ZXMP6A17D	7	12	500

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
 5. For packaging details, go to our website at <http://www.diodes.com>

Marking Information


ZXMP6A17D = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 11 = 2011)
 WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

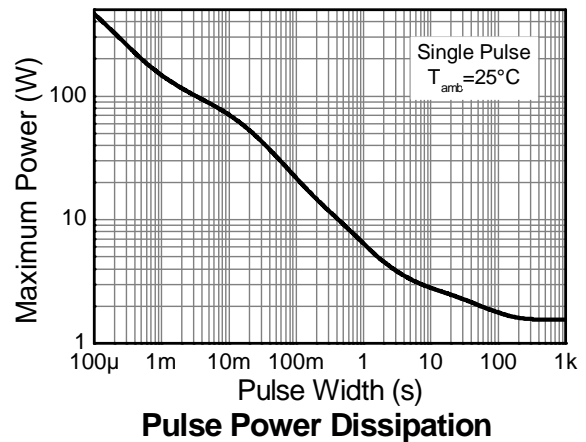
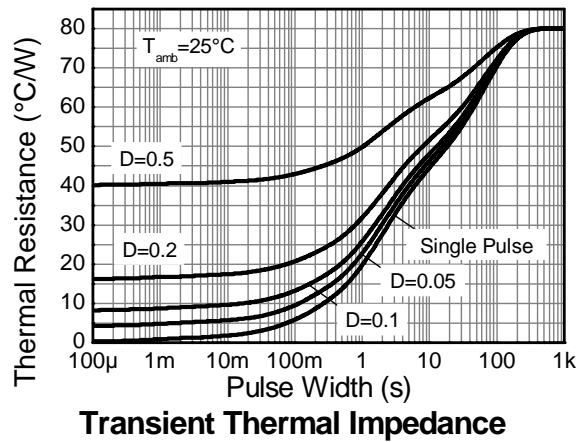
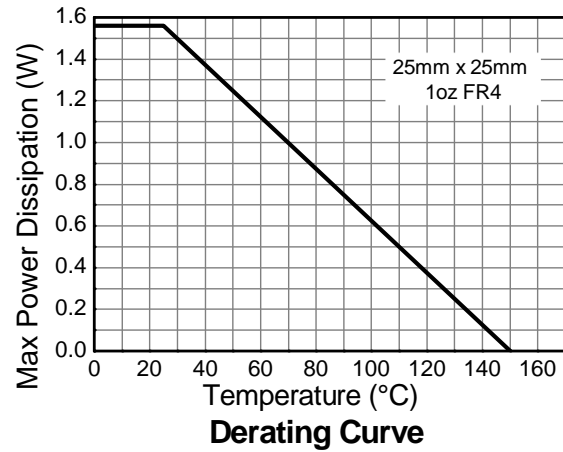
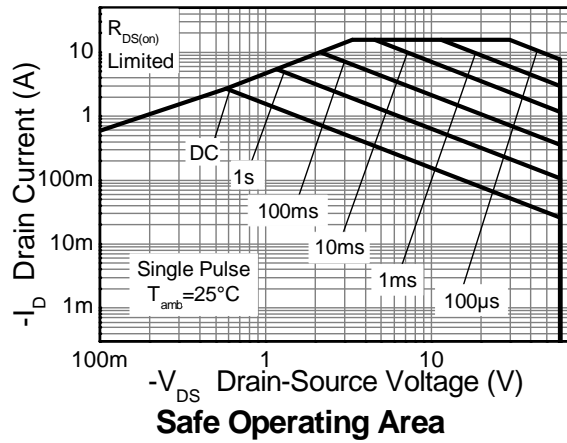
Characteristic			Symbol	Value	Unit
Drain-Source voltage			V _{DSS}	-60	V
Gate-Source voltage			V _{GS}	±20	V
Continuous Drain current	V _{GS} = 10V	(Notes 7 & 9)	I _D	-3.42	A
		T _A = 70°C (Notes 7 & 9)		-2.73	
		(Notes 6 & 9)		-2.7	
Pulsed Drain current		(Notes 8 & 9)	I _{DM}	-15.6	A
Continuous Source current (Body diode)		(Notes 7 & 9)	I _S	-3.4	A
Pulsed Source current (Body diode)		(Notes 8 & 9)	I _{SM}	-15.6	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Notes 6 & 9)	P _D	1.25	W
	(Notes 6 & 10)		10.0	
	(Notes 7 & 9)		1.81	
	(Notes 6 & 10)		14.5	
Thermal Resistance, Junction to Ambient	(Notes 6 & 9)	R _{θJA}	2.15	°C/W
	(Notes 6 & 10)		17	
	(Notes 7 & 9)		100	
Thermal Resistance, Junction to Lead	(Notes 6 & 10)	R _{θJL}	70	°C/W
	(Notes 7 & 9)		60	
	(Notes 9 & 11)		51.68	
Operating and storage temperature range		T _J , T _{STG}	-55 to 150	°C

- Notes:
6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 7. Same as note (6), except the device is measured at t ≤ 10 sec.
 8. Same as note (6), except the device is pulsed with D = 0.02 and pulse width 300μs. The pulse current is limited by the maximum junction temperature.
 9. For a dual device with one active die.
 10. For a device with two active die running at equal power.
 11. Thermal resistance from junction to solder-point.

Thermal Characteristics

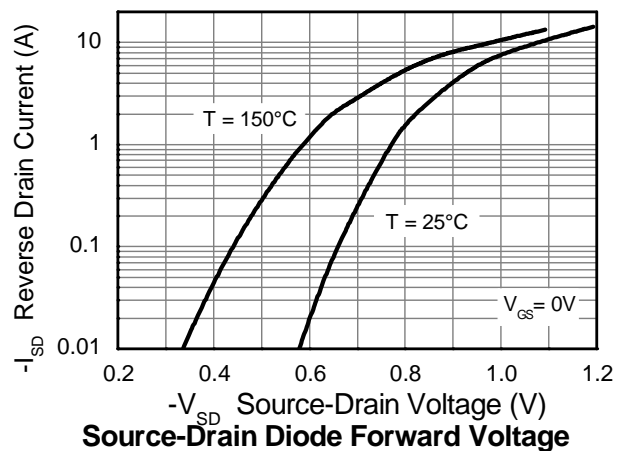
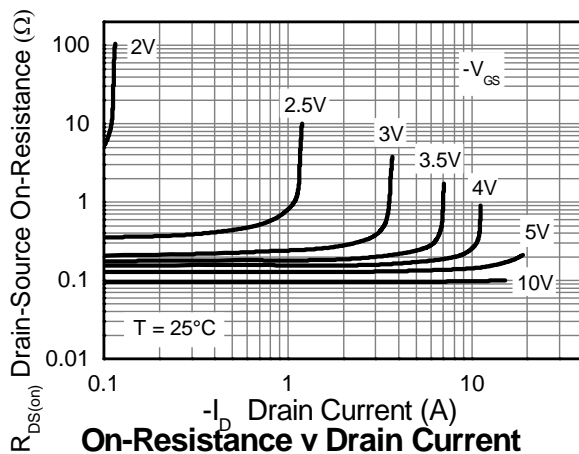
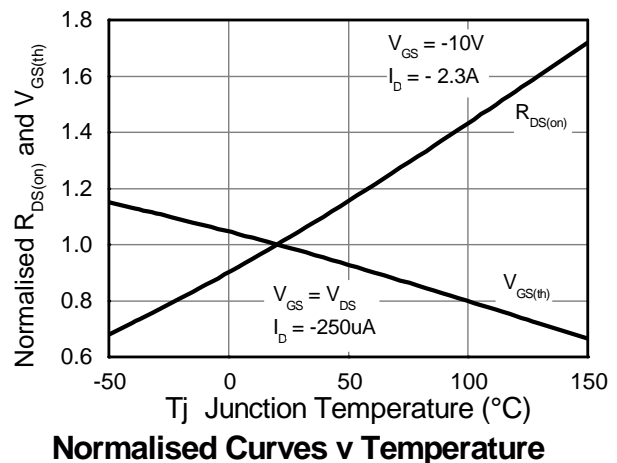
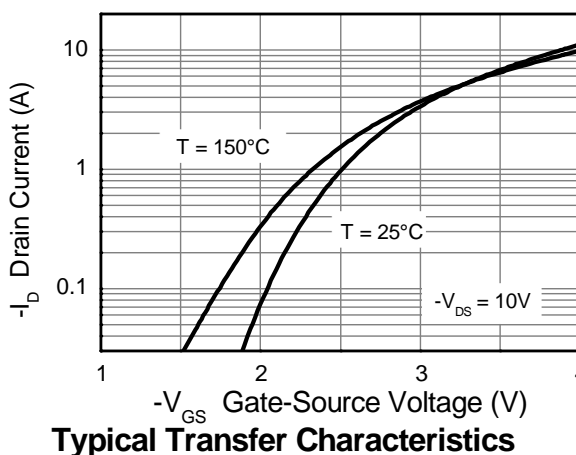
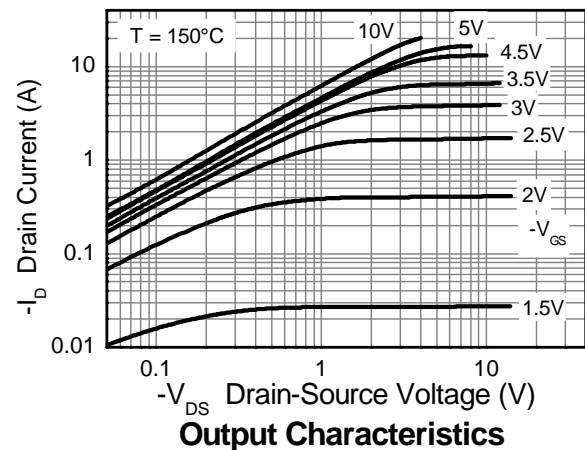
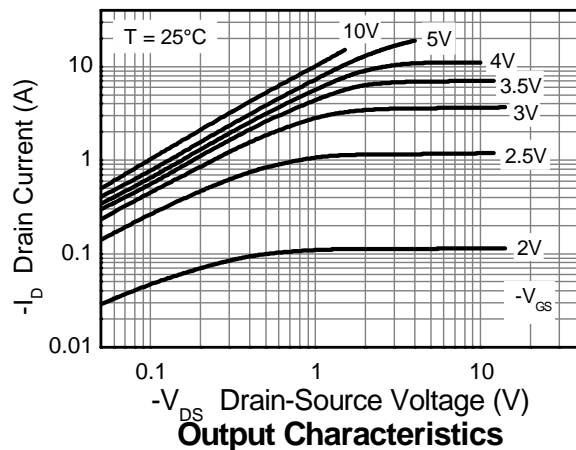


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

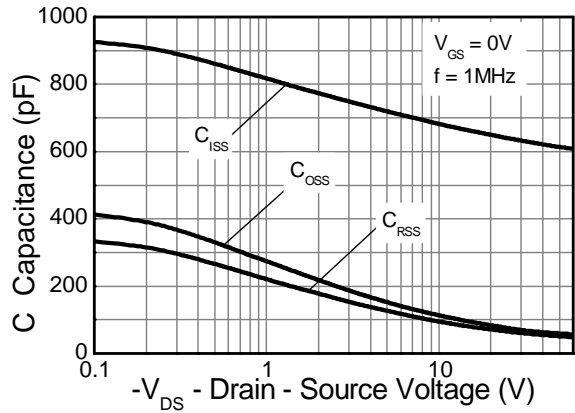
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	I _D = -250μA, V _{GS} = 0V	
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-0.5	μA	V _{DS} = -60V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	-1.0	—	—	V	I _D = -250μA, V _{DS} = V _{GS}	
Static Drain-Source On-Resistance (Note 12)	R _{DS (ON)}	—	—	0.125	Ω	V _{GS} = -10V, I _D = -2.3A	
				0.190		V _{GS} = -4.5V, I _D = -1.9A	
Forward Transconductance (Notes 12 & 13)	g _{fs}	—	4.7	—	S	V _{DS} = -15V, I _D = -2.3A	
Diode Forward Voltage (Note 12)	V _{SD}	—	-0.85	-0.95	V	I _S = -2.0A, V _{GS} = 0V	
Reverse recovery time (Note 13)	t _{rr}	—	25.1	—	ns	I _S = -1.7A, di/dt = 100A/μs	
Reverse recovery charge (Note 13)	Q _{rr}	—	27.2	—	nC		
DYNAMIC CHARACTERISTICS (Note 13)							
Input Capacitance	C _{iss}	—	637	—	pF	V _{DS} = -30V, V _{GS} = 0V f = 1MHz	
Output Capacitance	C _{oss}	—	70	—	pF		
Reverse Transfer Capacitance	C _{rss}	—	53	—	pF		
Total Gate Charge (Note 14)	Q _g	—	9.0	—	nC	V _{GS} = -4.5V	V _{DS} = -30V I _D = -2.2A
Total Gate Charge (Note 14)	Q _q	—	17.7	—	nC	V _{GS} = -10V	
Gate-Source Charge (Note 14)	Q _{gs}	—	1.6	—	nC		
Gate-Drain Charge (Note 14)	Q _{gd}	—	4.4	—	nC		
Turn-On Delay Time (Note 14)	t _{D(on)}	—	2.6	—	ns	V _{DD} = -30V, V _{GS} = -10V I _D = -1A, R _G ≅ 6.0Ω	
Turn-On Rise Time (Note 14)	t _r	—	3.4	—	ns		
Turn-Off Delay Time (Note 14)	t _{D(off)}	—	26.2	—	ns		
Turn-Off Fall Time (Note 14)	t _f	—	11.3	—	ns		

- Notes:
- Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
 - For design aid only, not subject to production testing.
 - Switching characteristics are independent of operating junction temperatures.

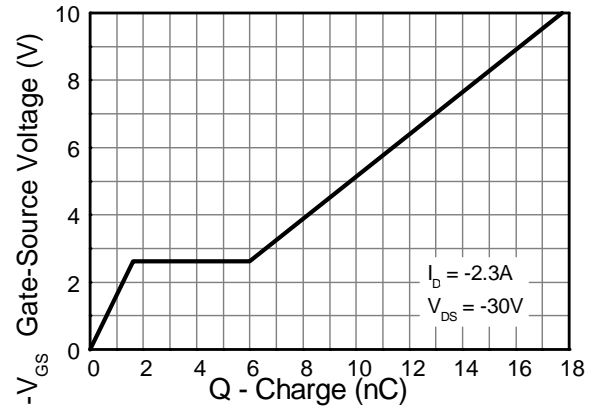
Typical Characteristics



Typical Characteristics - continued

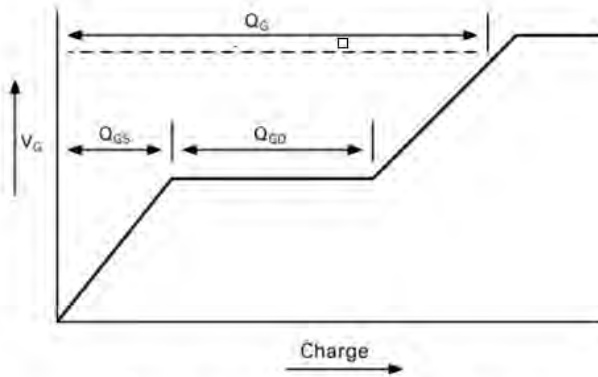


Capacitance v Drain-Source Voltage

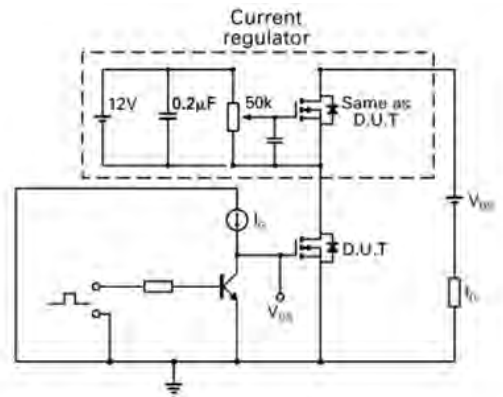


Gate-Source Voltage v Gate Charge

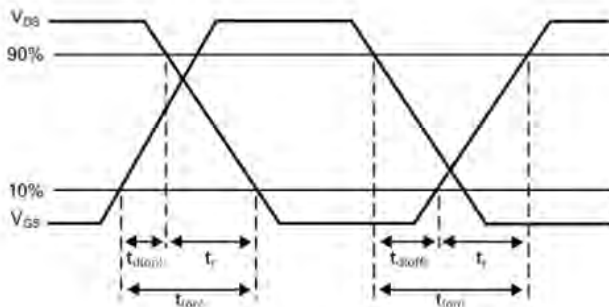
Test Circuits



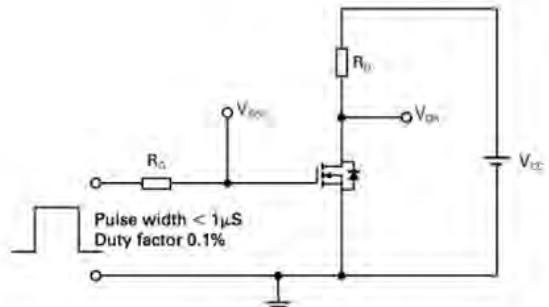
Basic gate charge waveform



Gate charge test circuit



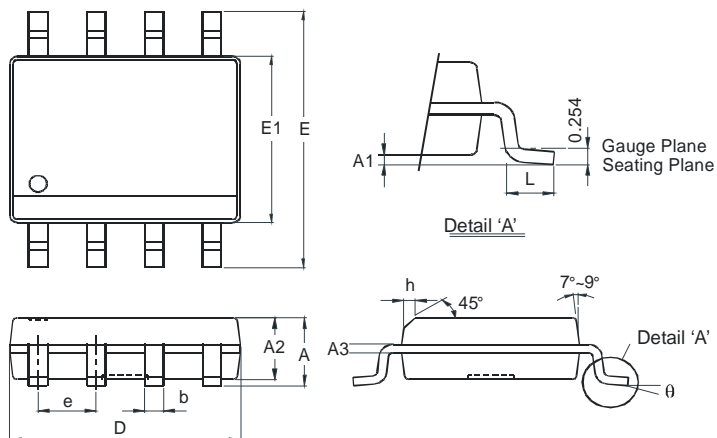
Switching time waveforms



Switching time test circuit

Package Outline Dimensions

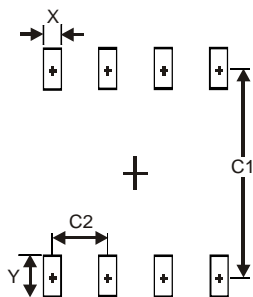
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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